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{Chemical Formula 2}

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20. (Original) The method of claim 19, wherein components B and C are selected independently from groups shown in chemical formula 3, substituted-structure groups of the chemical formula 3 with a halogen, cyano, nitro, amino group, other substituted-structure groups

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ethenyl group, is selected from groups designated in chemical formula 2, substituted-structure groups of chemical formula 2 with a halogen, cyano, nitro, amino group, and other substituted-structure groups with a alkyl and haloalkyl, and cyanoalkyl group having 1 to 10 carbons or an aryl, alkyl, aryl, haloaryl, haloalkyl aryl, nitroaryl, cyanoaryl group having 3 to 8 carbons; {Chemical Formula 2}

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27. (Original) The method of claim 26, wherein components B and C are selected from groups shown in chemical formula 3, substituted-structure groups of chemical formula 3 with a halogen, cyano, nitro, amino group, other substituted-structure groups with carbonated groups of which carbon number n lies between 1 and 10 such as an alkyl, haloalkyl, and cyanoalkyl, and other carbonated groups of which carbon number lies between 3 and 8 such as an alkylaryl, haloalkyl aryl, nitroaryl, cyanoaryl;

{Chemical Formula 3}

$$\begin{array}{c} \text{-(CH}_{2})_{a}, \quad -0-, \quad -\text{C00-}, \quad -\text{NHC0-} \\ \text{-CH}_{3} \\ -\text{NHC0-}, \quad -\text{CH}_{2}\text{CHC0-} \\ \text{-(CH}_{2}\text{O})_{\overline{a}}, \quad \text{-(CH}_{2}\text{CH}_{2}\text{O})_{\overline{a}}, \quad \text{-(CH}_{2})_{a}\text{O-} \\ \text{-(CH}_{2}\text{O})_{\overline{a}}, \quad \text{-(CH}_{2}\text{CH}_{2}\text{O})_{\overline{a}}, \quad \text{-(CH}_{2}\text{-}\bigcirc \\ \text{-(CH}_{2}\text{O})_{\overline{a}}, \quad \text{-(CH}_{2}\text{-}\bigcirc \\ \\ \text{-(CH}_{2}\text{-}\bigcirc \\ \text{-(CH}_{2}\text{-}\bigcirc \\ \\ \\ \text{-(CH}_{2}\text{-}\bigcirc \\ \\ \\ \text{-(CH}$$

28. (Original) The method of claim 25, further comprising:

forming a gate line and a crossing data line on the first substrate;

forming a thin film transistor at a crossing between the gate and data lines; and forming a pixel electrode connected to the thin film transistor.